BITS-Pilani Dubai, Dubai International Academic City, Dubai III Yr. B.E.(Hons.) First Semester Academic Year 2010 – 2011

COMPREHENSIVE EXAMINATION (Closed Book) - MICROELECTRONIC CIRCUITS

Course No.

: EEE C424 / ECE C313 / INSTR C313

Date

: 26.12.2010

: 120

Duration

: 3 Hrs

Max Marks

Weightage : 40%

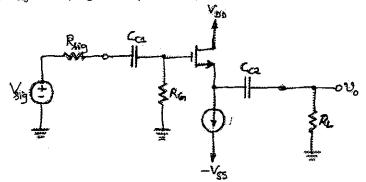
NOTE: 1. Answer Part A and Part B of each question in Two separate answer books.

2. Make assumptions, if any, but explicitly indicate the assumptions made.

PART A

1) With a neat circuit diagram of a single stage CG amplifier and using its small signal analysis derive an expression for (a) an overall voltage gain, (b) input resistance and (c) output resistance (10 M)

2) For the circuit shown below, find R_{in} , A_{vo} , A_v , G_V and R_{out} , both (a) with r_0 and (b) without r_0 . if $g_m=1mA/V$, $r_0=100K\Omega$, $R_{siq}=2M\Omega$, $R_L=30K\Omega$ and $RG=4.7M\Omega$



(6+4=10M)

- 3) Starting from fundamentals derive an expression for f_T of a typical MOSFET. Also calculate the same if the device's V_{OV} =0.25V, C_{gs} =20fF, C_{gd} =5fF and is operating at I_D =100 μ A. (6+2=8M)
- 4) Draw the (a) circuit diagram of a BJT differential amplifier and (b) its transfer characteristics. Also explain why the shape for the transfer characteristics. (6M)
- Design a Butterworth low-pass filter to have: f_p=10KHz, A_{max}=2dB, f_s=15kHz, and A_{min}=15dB. Estimate the attenuation it provides at 20kHz.
- 6) Neglecting the effects of finite V_{BE} and V_{CEsat} find:

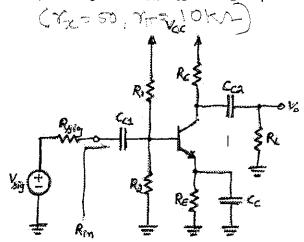
(2+2+2=6M)

- a) maximum sine wave output power available
- b) average power drawn from each of the power supplies and
- c) power conversion efficiency

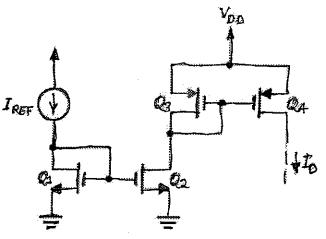
of a Complementary BJT class B output stage having $\pm 10V$ power supply and a 100Ω load resistance.

- 7) It is required to ensure safe operation at 30W of a power transistor which at T_{Jmax}=180°C can dissipate 50W at a case temperature of 50°C. Find the (3+3+2=8M)
 - a) necessary heat sink temperature, if the device is connected to a heat sink using an insulating washer whose thermal resistance of 0.6°C/W.
 - b) required thermal resistance of the heat sink, if ambient temperature is 40°C.
 - c) length of the required extruded-aluminum-finned heat sink, whose thermal resistance in still air is 4.5°C/W per centimeter of its length?

- 1) A BJT whose β = 220 is biased to operate in the active mode at a dc collector current of 2.0 mA. Draw each of following model and compute its parameters: (2.5x4=10M)
 - a) Simplified hybrid-π VCCS model
 - b) Simplified hybrid-π CCCS model
 - c) VCCS representation of T-model
 - d) CCCS representation of T-model
- 2) For the amplifier in the figure below whose component values are: R_{sig} =5 $K\Omega$, R_1 =39 $K\Omega$, R_2 =27 $K\Omega$, R_E =3.3 $K\Omega$, R_C =4.7 $K\Omega$, R_L =5.6 $K\Omega$, R_C =10V, let R_C =10V, let R_C =25V=100 and R_C =300V=100 and R_C =300V=300 and R_C =300 and R_C

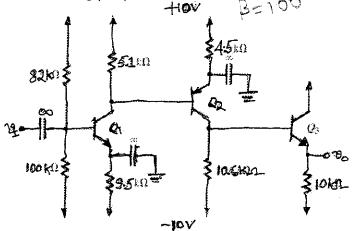


3) For the current steering circuit shown in figure below, find Io in terms of I_{REF} and device (W/L) ratios.



CIOM)

4) Figure below shows a three stage amplifier in which the stages are directly coupled. Neglecting early effect and assuming $|V_{BE}|=0.6V$, find the (5x2=10M)



- a) dc bias current in each of the three transistors and
- b) dc voltage at the output.
- c) input resistance
- d) output resistance
- e) voltage gain v_o/v_i
- 5) a) An amplifier with open-loop voltage gain A_V =1500 \pm 150 is available. It is necessary to have an amplifier whose voltage gain more than \pm 0.2%. Find the reverse transmission factor β of the feedback network used and also the gain with feedback. (4M) b) A series-shunt feedback amplifier employs a basic amplifier with input and output resistances of 1.5K Ω each and gain of A = 1500 V/V. The feedback factor is 0.2 V/V. Find A_f , R_{if} and R_{of} of the closed-loop amplifier. (1+1.5+1.5=4M)
- 6) An amplifier has a dc gain of 10^5 and poles at 10^5 Hz, and $3.16x10^5$ Hz and 10^6 Hz. Find the value of β and the corresponding closed loop gain for which a phase margin of 45° is obtained. (6M)
- 7) Illustrate the structure and special features of the following compound devices (a)Darlington pair (b)Totem-pole Configuration and (c) Cascode amplifier (3+2+3=8M)

****) ALL THE BEST(****

BITS-Pilani Dubai, International Academic City, Dubai I - Semester Academic Year 2010-11

Evaluation Component: TEST - II (Open Book) EEE C424 / ECE C313 / INSTR C313 MICROELECTRONIC CIRCUITS

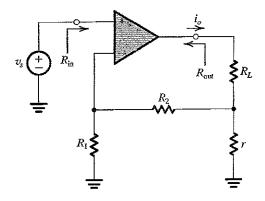
Date: 21st November 2010

Maximum Marks: 60

Duration: 50 mts.

Weightage :20%

- Note:- 1. ANSWER ALL the Questions with "most appropriate answer(s)"
 - 2. Wherever required, make reasonable assumptions and indicate explicitly the assumptions made, if any.
 - 3. Use Semi-log Graph sheet, wherever required.
- Identify the (a)Feedback topology and (b)the circuit elements that constitute feedback network in the feedback amplifier circuit shown the figure below. Compute (c) Transfer gain(A_f) of the feedback amplifier; and the values of (d)Rin & (e)Rout - as shown in the figure assuming OPAMP's internal parameters as: open loop voltage gain (μ)=10⁵ V/V; differential input resistance (R_{id}) =10K Ω ; output resistance r_0 =100 Ω and given that: R_L =1K Ω , r=100 Ω , R_2 =1K Ω and $R_1=100\Omega$. If R_1 is made infinite and OPAMP's μ drifts to it's a new value = 10^4 V/V, also find (f)A_f, (g)R_{in} and (h)R_{out}. (0.5+0.5+3x3+2x3=16M)



- 2. An NMOS differential amplifier is operated at a bias current of I of 0.5 mA and has W/L ratio of 50, $\mu_n C_{ox}$ = 250 μ A/V², V_A = 10V and R_D is 4K Ω find V_{ov} , g_m , r_o and A_d . (5M)
- 3. A dc amplifier has two poles and an open loop gain of 1000. One of the poles is at 1 KHz (the dominant one) while the other is at a location controllable by the designer. Find the β and the required value of pole if this amplifier is required to be connected in a negative feedback loop to provide a dc closed loop gain of 100 and a maximally flat response. (5+5=10M)
- 4. Sketch the polar plot of the loop gain βA, indicating in each case whether or not the closed loop amplifier is stable, for a three-pole feedback amplifier with a dc gain (without feedback) A_o = -1000, and open-loop poles at f_1 =0.5 MHz, f_2 =1MHz, and f_3 =2 MHz assuming (a) β = -0.005; (b) β = - 0.02; (c) Also find the maximum value of β for which the amplifier is stable? (3+3+3=9M)
- 5. A three-pole feedback amplifier has a dc gain without feedback of -10⁴. All the three open-loop poles are at f=2 MHz. (a) what is the maximum value of β for which the amplifier is stable? (b) If one of the poles is shifted to f_1 =100 KHz, using the value of β found in (a) compute the gain (5+5=10M)margin of the modified circuit.
- 6. For NMOS differential pair with common mode voltage v_{CM} applied as shown in the assuming $V_{DD}=V_{SS}=2.5V k_n$ W/L=3mA/V². $V_t=0.7V$, I=0.2mA, $R_D=5K\Omega$ and neglect the channel length modulation. Find (a) Find V_{OV} and V_{GS} for each transistor (b) v_s , i_{D1} , v_{D1} and v_{D2} if $V_{CM}=0$ (c) Repeat (b) for v_{CM} =+1V, (d) Repeat (b) v_{CM} =-1V, (e) What is the highest value of v_{CM} for which Q₁ and Q₂ will remain in saturation? (5x2=10M)

BITS-Pilani Dubai, Dubai International Academic City, Dubai

III Yr. B.E.(Hons.) FIRST SEMESTER 2010 - 2011

TEST-I (Closed Book)

MICROELECTRONIC CIRCUITS

Course Code: EEE C424 / ECE C313 / INSTR C313

Date: 10.10.10

Course Title : Microelectronic Circuits

Max Marks: 60

Weightage: 20%

Duration

: 50 minutes

NOTE: 1. Answer ALL questions.

2. Make assumptions, if any, but explicitly indicate the assumptions made.

- 1) Define any SIX of the following terms with reference to electronic amplifier circuits:
 - (i) Voltage Gain
 - (ii) Bandwidth
 - (iii) Amplifier saturation
 - (iv) Maximum signal handling capacity
 - (v) Efficiency
 - (vi) AC Load Line
 - (vii) Amplifier Loading
 - (viii) Lower 3dB Frequency

(ix) Figure of merit

(6.0 M)

- 2) List the all the steps to perform low frequency small signal analysis of an amplifier circuit employing BJT or FET, indicating the typical assumptions made during the analysis. (4.0 M)
- 3) List any six important considerations in choosing the BIAS POINT while designing of a BJT (6.0 M)**Amplifier**
- 4) Draw the circuit of BJT Self Bias and Fixed Bias schemes. Justify why are the biasing schemes named so. (3+3=6M)
- 5) Derive an expression for magnitude response of Single Time Constant which do not attenuate low frequency components of the signal fed to its input and deduce an expression for its 3-dB cut-off (3+3=6.0 M)frequency.
- 6) Derive expressions for A_{ν} , $A_{\nu o}$, A_{is} and G_{ν} of a Common Emitter amplifier and indicate all characteristic changes due to inclusion of a small value of un-bypassed emitter resistance (6+3=9M)
- 7) A BJT Common Emitter Amplifier with R_c =10 k Ω is connected between a source with R_s =5 k Ω , and a load of R_L=5 k Ω . Assuming that the parameters of the BJT model are: r_n =2.5 k Ω , $q_m=40$ mA/V, $r_0=100$ k Ω ,

a) Derive an expression for overall voltage gain

(3M)

b) Find the magnitude of overall voltage gain.

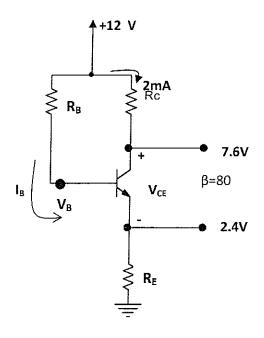
(3M)

c) Recalculate the magnitude of overall voltage gain neglecting ro

(3M)

(Please Turn Over)

- 8) Draw the h-parameter model of a BJT used in CE Configuration and define all the four parameters, and indicate how each of the four model parameters can be obtained from BJT characteristics. (1+1+4=6 M)
- 9) Given the following Circuit shown in Fig. 1. below, find R_C , R_E , R_B , V_{CE} , V_B (1.5x4+2=8M)



ALL THE BEST

BITS-Pilani Dubai, Dubai International Academic City, Dubai III Yr. B.E.(Hons.) FIRST SEMESTER 2010 - 2011

QUIZ -2

MICROELECTRONIC CIRCUITS

Course Code: EEE C424 / ECE C313 / INSTR C313

Date: 14.12.10

Course Title: Microelectronic Circuits

Max Marks: 30

Duration

: 50 minutes

Weightage: 10%

NOTE: 1. Answer ALL questions.

2. Make assumptions, if any, but explicitly indicate the assumptions

Q1) Identify the incorrect statements with respect to multistage amplifier (2M)

a. Output stage is always a differential amplifier.

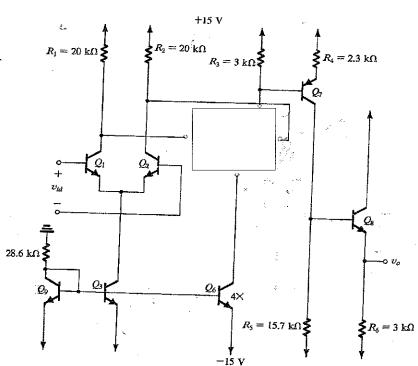
b. DC level shifting is done in the intermediate stage

c. Input stage is responsible for the bulk gain

d. Output stage is a power amplifier

Q2) Complete the following circuit diagram by drawing the missing circuit elements in square mark

(2M)

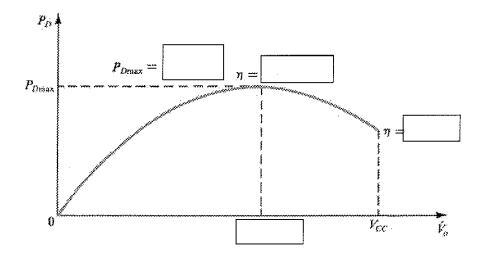


Q3)What is the overall 3dB frequency of six non interacting cascading stages of high pass filters, each having 3dB high frequency of 5KHz (2M)

Ans:

Q4) Draw a	Darlington pair using	g BJT		(1M)···
,			nree stage cascaded tan output voltage of	•
Ans:				
Q6) Define	Fotal Harmonic Disto	ortion (THD) in one sentence.	(1M)
Q7) Draw th	e collector current w	aveform fo	r the Class B Amplifie	r (1M)
			on efficiency of class <i>i</i>	-
	ofis			(3M)
Q9) For the	class B output stage	e amplifier	V_{cc} =10V, and RL=20	Ω . If the output
is sinusoid w	ith 6.5 V peak ampli	tude, Find		(1x4=4M)
a.	The output power	=	_	
b.	Average power dra	wn from ea	ach supply=	
C.	The power efficience	cy obtained	at this output stage=	
d.	The peak current se	upplied by	V _I , assuming β _N =100=	

Q10) Fill the required answers in the square boxes shown in the following figure, which shows the power dissipation of a class B output stage versus amplitude of the output sinusoid. (1X4=4)

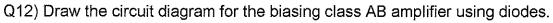


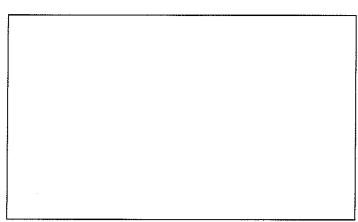
Q11) A BJT is specified to have T_{JMAX} =100°C, and to be capable of dissipating maximum power of 40W at T_{C} =25°C and 2W at T_{A} =25°C. Above 25°C, the maximum power dissipation is to be derated linearly with θ_{JC} =2.12°C, and θ_{JA} =60.5°C. Find

a. The maximum power that can be dissipated safely by this transistor, when operated in the free air at 45°C.

Ar	ns:
b.	The maximum power that can be dissipated safely by this transistor when
	operated at an ambient temperature of 50°C, but with a heat sink for which
	θ_{CS} =0.4°C/W and θ_{SA} =3°C/W.
Δn	os.

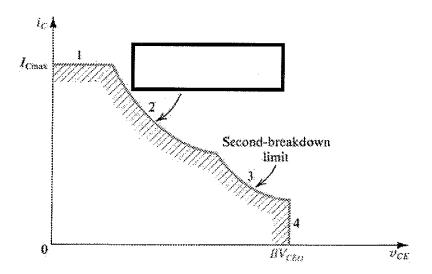
(1+2=3M)





Q13) In class B amplifier , there exist a range of input voltage v_l centered around zero where both the transistor are cut off and v_0 is ______. This _____ results in the cross over distortion. (2M)

Q14) Following is a safe operating area of BJT, fill the proper answer for the region 2 in the square box shown. (1M)



BITS-Pilani Dubai, Dubai International Academic City, Dubai III Yr. B.E.(Hons.) FIRST SEMESTER 2010 – 2011

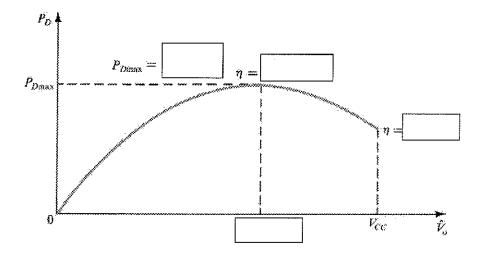
QUIZ -2

MICROELECTRONIC CIRCUITS

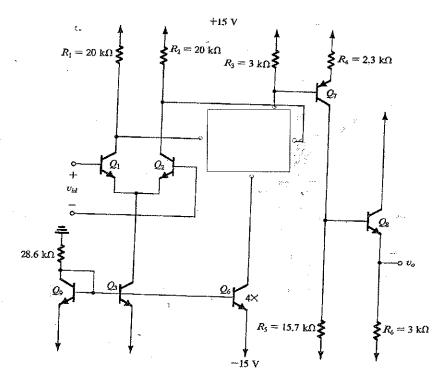
Course Title Duration	e: EEE C424 / ECE C313 / INSTR C313 : Microelectronic Circuits : 50 minutes 1. Answer ALL questions.		Date : 14. ′ Max Marks Weightage	s: 30
	2. Make assumptions, if any	, but explicit	ly indicate the	assumptions
Q1) For the	class B output stage amplifie	r V _{cc} =12V,	and R_L =25 Ω .	If the output
is sinusoid w	rith 6.5 V peak amplitude, Fin	d		(1x4=4M)
a.	The output power =			
b.	Average power drawn from 6	each supply:	=	_
C.	The power efficiency obtained	ed at this out	:put stage=	
d.	The peak current supplied b	y V _I , assumi	ng β _N =100=	
Q2)What is t	he overall 3dB frequency of fo	our non inte	racting cascac	ling stages of
high pass filt Ans:	ers, each having 3dB high fre	quency of 5	KHz	(2M)
Q3) Draw a I	Darlington pair using FET			(1 M)
	input voltage required to a tage having 30dB of gain, to ge			
Ans:				
Q5) Define T	otal Harmonic Distortion (THI	O) in one ser	ntence.	(1M)

ion efficiency of class A amplifier is	conversion ef	for the power	Q7) Expression for
conditions maximum		_, and under	,
ned. (3M	is obtained.		efficiency of

Q8) Fill required answers in the square boxes shown in the following figure, which shows the power dissipation of a class B output stage versus amplitude of the output sinusoid. (1X4=4)



Q9) In class B amplifier , there exist a range of input voltage v_1 centered around zero where both the transistor are cut off and v_0 is ______ This dead band results in the _____. (2M)



Q11) A BJT is specified to have T_{JMAX} =100°C, and to be capable of dissipating maximum power of 40W at T_{C} =25°C and 2W at T_{A} =25°C. Above 25°C, the maximum power dissipation is to be derated linearly with θ_{JC} =2.12°C, and θ_{JA} =60.5°C. Find

a. The maximum power that can be dissipated safely by this transistor, when operated in the free air at 45°C.

Ans: _____

b. The maximum power that can be dissipated safely by this transistor when operated at an ambient temperature of 50°C, but with a heat sink for which θ_{CS} =0.4°C/W and θ_{SA} =3°C/W.

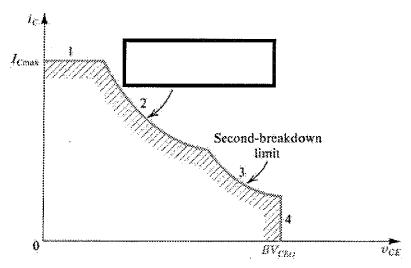
Ans:	
	T

(1+2=3M)

Q12) Draw the circuit diagram for the biasing class AB amplifier using diodes. (2M)



Q13) Following is safe operating area plotted on i_{C} - v_{CE} characteristics of a BJT, fill the proper answer for the region 2 in the square box shown. (1M)



Q14) Identify the incorrect statements with respect to multistage amplifier

(2M)

- a. DC level shifting is done in the intermediate stage
- b. Input stage is responsible for the bulk gain
- c. Output stage is a power amplifier
- d. Output stage is always a differential amplifier.

Stude	ent Name:					BITS ID			
		BITS-P	ilani Dubai, I		al Academi Year 2010-1		ubai		$\overline{\mathbf{A}}$
			Evaluation	on Component	QUIZ - I				<i>A</i>
Date :	E 3 rd November 2		ECE C313 / INS	STR C313 MI	CROELECT		IRCUITS Maximum M	Iarks: 30	
	on: 25 mts.						Weightage	:10%	
		Note:-	1.Respond ALL 2. Provide "mos		e answer(s)"	for each qu	estion.		
			3. Indicate expli	icitly the assu	mptions if any	·			
			4. All questions	carry I mark	uniess otnerw	ase maicat	ea		
			ck amplifier's						(1M)
2.		_	feedback top					nding ter	
	under II	by indica	ting the seria	ino. of fi	n the brace	es: "[]"	OT II.		(2M)
		1			11				
		ies Series			nixing and			[]
		nt Series Int Shunt			nixing and			[]
		ini Shunt ies Shunt			nixing and nixing and			<u>L</u> T]]
3.	In a MOSF	ET , the t	thickness of t	the oxide l	ayer is 10	nm, and	permittivit		1
	silicon diox	kide is 3.4	15x10 ⁻¹¹ F/m,	what is th	ie capacita	ince per	unit area	C _{ox.}	(2 M)
	la au FFT			44!					_
4.	ın an ⊦⊨ı, which i⊳ is	expressi	on for i _D in th	ne saturation	on region i: ·	s:	· \//	II ' is:	1
		; L is	3:	; V _{GS}	 is :			$_$ and V_t	is:
			····				((1+0.5x6	=4M)
5.			e distinguishir Frue" or "Fals						
	•		s lesser spac	•		_	[71. (0141)]
			nmune to noi				į		j
			es more pow high input res				Į r		j 1
			gher voltage]
	F. FET	do not o	ffer response	without a	stimulus u		•		j
6.			a CS amplific		ng a devic	e whose	$g_{\rm m} = 10 {\rm n}$		
7.			ົΩ and R _D =1 ency Hybrid-₁		a MOSEE	T in whi	 ch hody et		(1 M)
••			e is connecte			1 117 44711	on body of		(3 M)
8.	•	•	en-loop gain		_			-	
	an amplifie	r whose \	∕oltage gain י	varies by r	o more tha	an <u>+</u> 0.1	percent. F	•	
								(2 M)

loop is broken and a test Open & Short circuit tran expressions to find T _{oc} and	nsfer functions			
Αβ =	; T _{sc} =	; T _{oc} =		where in
				_ ;
is	;	_ is		_
 10. If the two poles of a feedbarnature then they occur as a 11. Identify the feedback topo space provided below. If greedback amplifier. 	a respon blogy of the cir	pair an ise. cuit given be	d the amplifier is slow. Draw the A 100; Compute A	s said to have (0.5+0.5=1M) A Circuit in the
$R_{c} = 4.7 \text{ k}\Omega$ $R_{s} = 10 \text{ k}\Omega$ $R_{s} = \frac{10 \text{ k}\Omega}{R_{s}}$	A Circuit i	<u>s</u> :		
****	[· · · · · · · · · · · · · · · · · · ·			
(8)	A =		β =	
12. The Gain Margin is defined angle of is			in dB at wh	ich the phase (1.5 M)
angle of is is is	is unity. of a feedback ne amplifier will n of a feedbacl	c amplifier, if be unstable. c amplifier ha	the Nyquist plo	(1.5 M) ot of
Root-Locus	s-Diagram		A comment o Stability of the	

9. In determining the loop gain $\ensuremath{\mathsf{A}\beta}$ through an approach in which conceptual feed back

* * * * ALL THE BEST * * * *

Student Name:	BITS ID No.:
BITS-Pilani Du	bai, International Academic City, Dubai
	Semester Academic Year 2010-11
EEE C424 / ECE C313	valuation Component: QUIZ - I B / INSTR C313 MICROELECTRONIC CIRCUITS
Date: 3 rd November 2010	Maximum Marks: 30
Duration: 25 mts. Note:- 1.Respon	Weightage :10%
2. Provid	e "most appropriate answer(s)" for each question.
	e explicitly the assumptions if any. estions carry 1 mark unless otherwise indicated
T. All qui	
	ck topology shown under I with the corresponding term serial no. of I in the braces: "[]" of II. (2M)
	II
A. Shunt Series	current mixing and voltage sampling []
B. Series Series	current mixing and current sampling []
C. Series Shunt D. Shunt Shunt	voltage mixing and voltage sampling []
2 In an FET expression for in	voltage mixing and current sampling [] in the saturation region is:
which, i _D is:	1 K _n ' is : : W is:
; L is:	; v _{GS} is : and V _t is:
	(1+0.5x6=4M)
3. Given below are the distinging amplifier, Indicate "True" or	uishing features of an FET over BJT for its use as an "False" in the parenthesis given against each. (3M)
	ponse without a stimulus unlike BJT [[[SiM]
	space during IC fabrication [
c. FET offers a high inp	
d. FET is less immune t	
e. FET consumes more f. FET offers higher vol	
4. In a MOSFET, the thicknes	s of the oxide layer is 10nm, and permittivity of the
silicon dioxide is 3.45x10 ⁻¹¹	F/m, what is the capacitance per unit area \hat{C}_{ox} (2 M)
5. Express the feedback ampli	fier's transfer gain, $A_f = $ (1M)
The Phase margin is	degrees minus at the
frequency at which	
	gy of the circuit given below. Draw the A Circuit in the
feedback amplifier.	is 60 mA/V; BJT's β_{dc} =100; Compute A and β for this (1+0.5+0.5=2 M)
+12 V	(170.070.07 <u>0.07</u>
***	A Circuit is:
₹ <i>R_c</i> ≈ 4.7 kΩ	
R _f = 47 kΩ	
$R_{\rm s} = 10 \text{ km}$	
"Y *	

(Please Turn Over)

	negligible (the source is connected to the substrate)	(3 M)
9.	An amplifier with open-loop gain Av=1,000±100 is available. It is necessar an amplifier whose voltage gain varies by no more than ±0.1 percent. Find	
10). In determining the loop gain $A\beta$ through an approach in which conceptual foop is broken and a test signal (as appropriate) is applied, express $A\beta$ in Open & Short circuit transfer functions (T_{oc} & T_{sc} respectively) and also expressions to find T_{oc} and T_{sc} . (0.5x)	terms of
	$A\beta =$; $T_{sc} =$; $T_{oc} =$	here in
11.	is	
	Root Locus Diagram Root Locus Diagram A comment on the Stability of the amplifier. A comment on the Stability of the amp	
13.	The Gain Margin is defined as the value ofin dB at which the angle of isdegrees. If the two poles of a feedback amplifier are on the imaginary axis and are cornature then they occur as a pair and the amplifier is said.	(1.5 M) nplex in
15.	The Voltage gain of a CS amplifier employing a device whose g_m = 10 mA/V; $K\Omega$ with an R_L =15 $K\Omega$ and R_D =1 $K\Omega$ is In determining the stability of a feedback amplifier, if the Nyquist plot ofencircles, the amplifier will be unstable.	-0.5=1M) r ₀ = 150 (1 M) (1 M)

8. Draw the high frequency Hybrid- π model of a MOSFET in which body effect is

* * * * ALL THE BEST * * * *